

**1A 20V(0.71mm)**

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**Chip Information**

Chip Size	0.71 x 0.71mm
Pad Size	0.60 x 0.60mm
Chip Quantity	21764 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	25	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	20	V	
Average Forward Rectified Current	IF(AV)	1000	mA	
Peak Forward Surge Current	IFSM	3	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.450		0.410	V	IF=1000mA Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	200	100	30	uA	VR=20V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	25	29	37	V	IR=600uA
Junction Capacitance	Cj			27	pF	VR=10V,f=1MHz
Reverse Recovery Time	trr				nS	

**Ordering Information**

Chip Type	Chip Thickness	Back Metal
YCG165	180 +/- 20um	Au(For Eutectic)
YCG167	150 +/- 20um	Au(For Eutectic)
YCG166	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:  
Designed For RB491D